

EAST - [10617719.wsp:1]

File View Edit Tools Window Help

Drafts
 Pending
 Active
 L1: (2) ("6469879").PN.
 L2: (0) ("ferromagneticadjlayer").PN.
 L3: (569) first adj ferromagnetic adj layer
 L5: (3) 4 and iridium adj manganese
 L4: (145) 3 and barrier
 Failed
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DBs: USPAT, EPO, JPO, DERWENT, IBM, TDB

Default operator: OR

Plurals

Highlight all hit terms initially

3 and barrier

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6661625 B1	20031209	15	Spin-dependent tunneling sensor with low resistance metal oxide tunnel barrier	360/324.2	
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6656538 B2	20031202	36	Method of manufacturing magnetoresistive device, method of manufacturing thin film	427/552	427/130; 427/131;
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6650513 B2	20031118	24	Magnetic devices with a ferromagnetic layer having perpendicular magnetic	360/324.2	
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6650512 B1	20031118	15	GMR coefficient enhancement of a spin valve structure	360/324.12	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6646530 B2	20031111	11	Configuration for minimizing the Neel interaction between two ferromagnetic	335/306	365/158; 365/171;
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6639830 B1	20031028	16	Magnetic memory device	365/158	365/171; 365/173
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6639766 B2	20031028	23	Magneto-resistance effect type composite head and production method thereof	360/324.2	29/603.14
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6639762 B2	20031028	53	Spin valve thin-film magnetic device having free magnetic layer in ferrimagnetic state	360/314	
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6639291 B1	20031028	9	Spin dependent tunneling barriers doped with magnetic particles	257/427	257/295; 257/421;
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6636436 B2	20031021	25	Isolation of memory cells in cross point arrays	365/158	257/295; 365/171;
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6636391 B2	20031021	19	Magnetoresistive sensor, magnetic head and magnetic disk apparatus	360/321	360/324.12